

Bias Resistor Transistors

PNP Silicon Surface Mount Transistors With Monolithic Bias Resistor Network

This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SC-89 package which is designed for low power surface mount applications.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- The SC-89 Package can be Soldered using Wave or Reflow.
- Available in 8 mm, 7 inch/3000 Unit Tape & Reel
- This is Pb-Free Device.

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Package	Shipping
LDTA114YET1	6D	SC-89 (Pb-Free)	3000/Tape&Reel

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

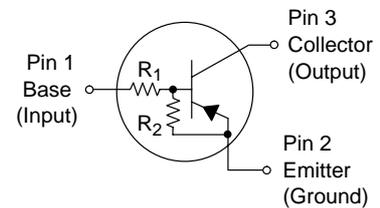
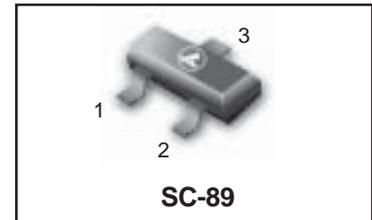
Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current	I _C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	200 (Note 1) 300 (Note 2) 1.6 (Note 1) 2.4 (Note 2)	mW mW/°C
Thermal Resistance – Junction-to-Ambient	R _{θJA}	600 (Note 1) 400 (Note 2)	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 x 1.0 inch Pad

LDTA114YET1



MARKING DIAGRAM



- xx = Specific Device Code
M = Date Code

LDTA114YET1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$)	I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$)	I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$)	I_{EBO}	–	–	0.2	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 3) ($I_C = 2.0\text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	–	–	Vdc

ON CHARACTERISTICS (Note 3)

DC Current Gain ($V_{CE} = 10\text{ V}, I_C = 5.0\text{ mA}$)	h_{FE}	80	140	–	
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$)	$V_{CE(sat)}$	–	–	0.25	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R_1	7.0	10	13	$\text{k}\Omega$
Resistor Ratio	R_1/R_2	0.17	0.21	0.25	

3. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

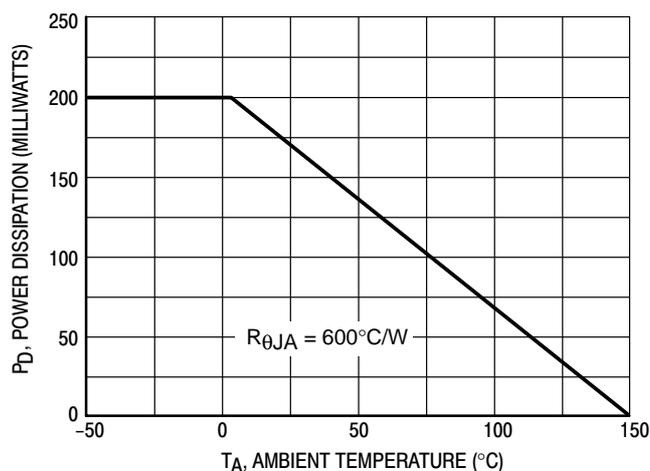


Figure 1. Derating Curve

LDTA114YET1

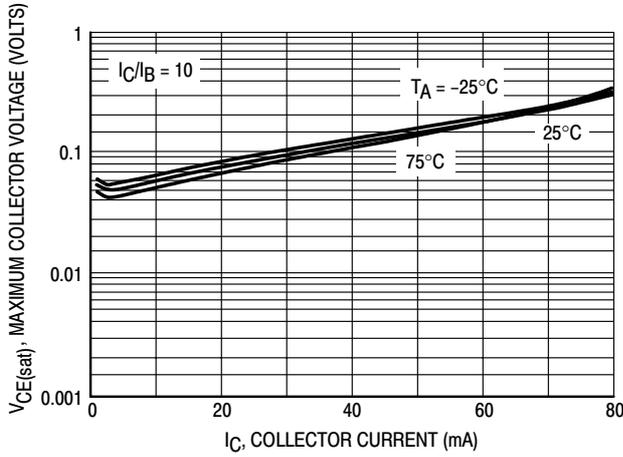


Figure 2. $V_{CE(sat)}$ versus I_C

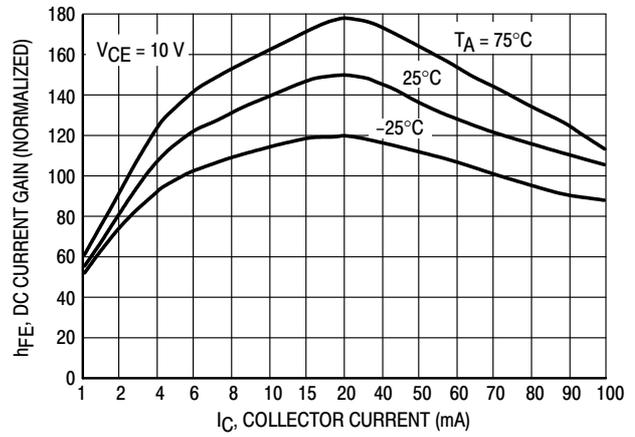


Figure 3. DC Current Gain

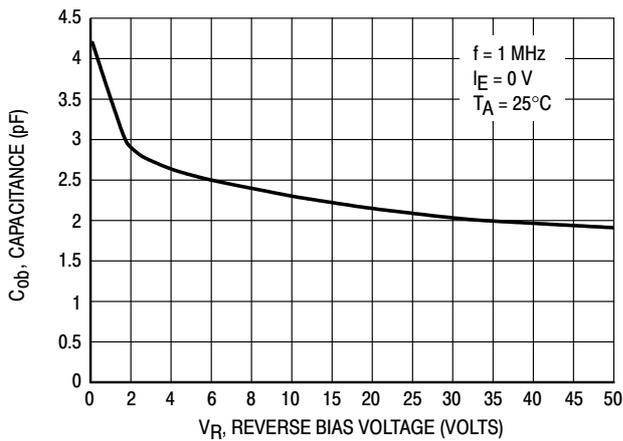


Figure 4. Output Capacitance

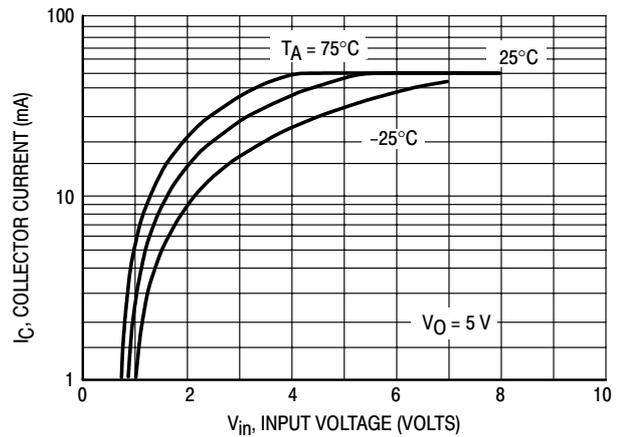


Figure 5. Output Current versus Input Voltage

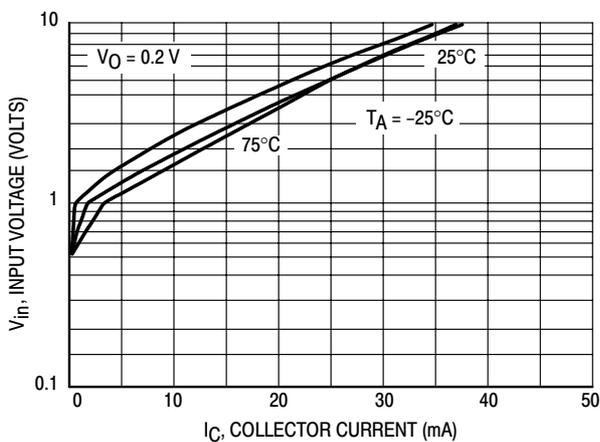


Figure 6. Input Voltage versus Output Current

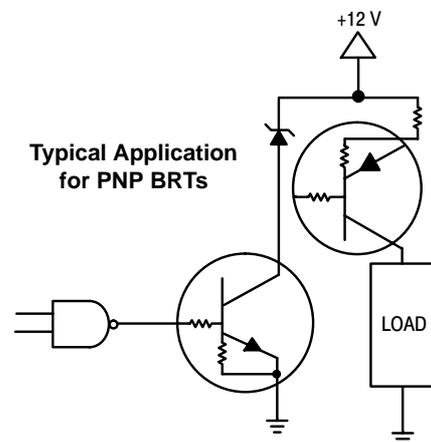
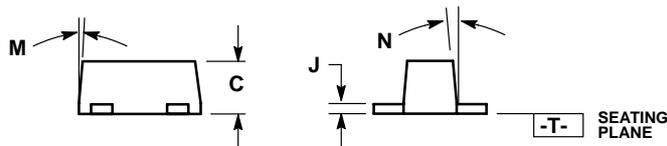
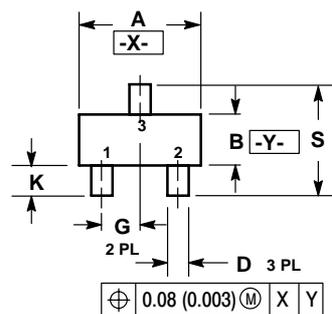


Figure 7. Inexpensive, Unregulated Current Source

LDTA114YET1

SC-89



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067

